



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



# MJE2955T (PNP), MJE3055T (NPN)

## Complementary Silicon Plastic Power Transistors

These devices are designed for use in general-purpose amplifier and switching applications.

### Features

- High Current Gain – Bandwidth Product
- These Devices are Pb-Free and are RoHS Compliant\*

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	60	Vdc
Collector–Base Voltage	$V_{CB}$	70	Vdc
Emitter–Base Voltage	$V_{EB}$	5.0	Vdc
Collector Current	$I_C$	10	Adc
Base Current	$I_B$	6.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$ (Note 1)	75 0.6	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

### THERMAL CHARACTERISTICS

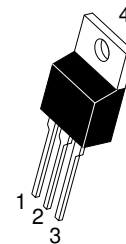
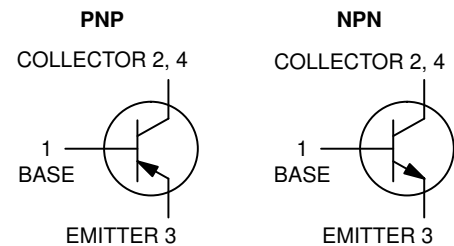
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.67	$^\circ\text{C}/\text{W}$



ON Semiconductor®

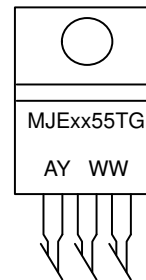
[www.onsemi.com](http://www.onsemi.com)

## 10 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60 VOLTS – 75 WATTS



TO-220  
CASE 221A-09  
STYLE 1

### MARKING DIAGRAM



MJExx55T = Device Code  
xx = 29 or 30  
G = Pb-Free Package  
A = Assembly Location  
Y = Year  
WW = Work Week

### ORDERING INFORMATION

Device	Package	Shipping
MJE2955TG	TO-220 (Pb-Free)	50 Units / Rail
MJE3055TG	TO-220 (Pb-Free)	50 Units / Rail

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## MJE2955T (PNP), MJE3055T (NPN)

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Sustaining Voltage (Note 2) (I <sub>C</sub> = 200 mAdc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	60	–	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	–	700	μAdc
Collector Cutoff Current (V <sub>CE</sub> = 70 Vdc, V <sub>EB(off)</sub> = 1.5 Vdc) (V <sub>CE</sub> = 70 Vdc, V <sub>EB(off)</sub> = 1.5 Vdc, T <sub>C</sub> = 150°C)	I <sub>CEX</sub>	– –	1.0 5.0	mAdc
Collector Cutoff Current (V <sub>CB</sub> = 70 Vdc, I <sub>E</sub> = 0) (V <sub>CB</sub> = 70 Vdc, I <sub>E</sub> = 0, T <sub>C</sub> = 150°C)	I <sub>CBO</sub>	– –	1.0 10	mAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	5.0	mAdc
<b>ON CHARACTERISTICS</b>				
DC Current Gain (Note 2) (I <sub>C</sub> = 4.0 Adc, V <sub>CE</sub> = 4.0 Vdc) (I <sub>C</sub> = 10 Adc, V <sub>CE</sub> = 4.0 Vdc)	h <sub>FE</sub>	20 5.0	100 –	–
Collector–Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 4.0 Adc, I <sub>B</sub> = 0.4 Adc) (I <sub>C</sub> = 10 Adc, I <sub>B</sub> = 3.3 Adc)	V <sub>CE(sat)</sub>	– –	1.1 8.0	Vdc
Base–Emitter On Voltage (Note 2) (I <sub>C</sub> = 4.0 Adc, V <sub>CE</sub> = 4.0 Vdc)	V <sub>BE(on)</sub>	–	1.8	Vdc
<b>DYNAMIC CHARACTERISTICS</b>				
Current–Gain–Bandwidth Product (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f = 500 kHz)	f <sub>T</sub>	2.0	–	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 20%.

# MJE2955T (PNP), MJE3055T (NPN)

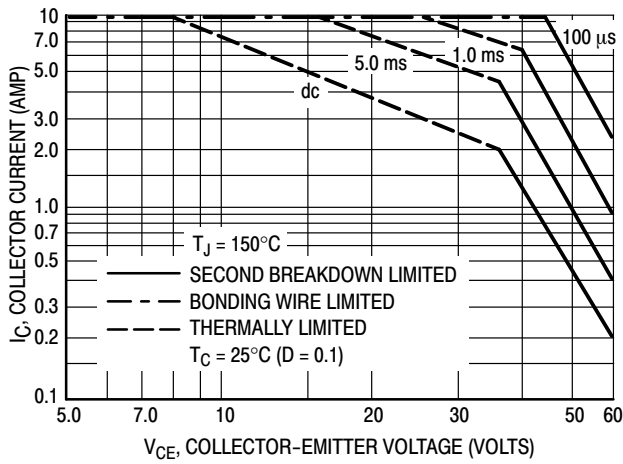


Figure 1. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on  $T_{J(pk)} = 150^\circ\text{C}$ .  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ . At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

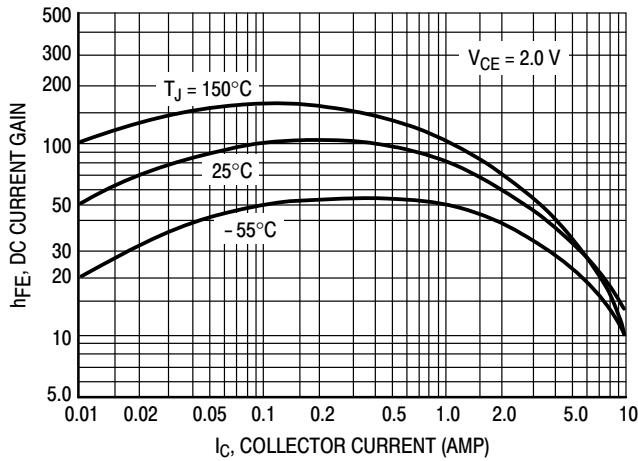


Figure 2. DC Current Gain

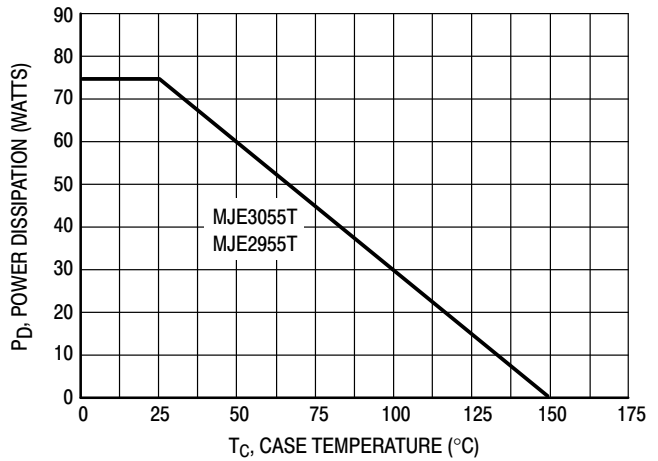


Figure 3. Power Derating

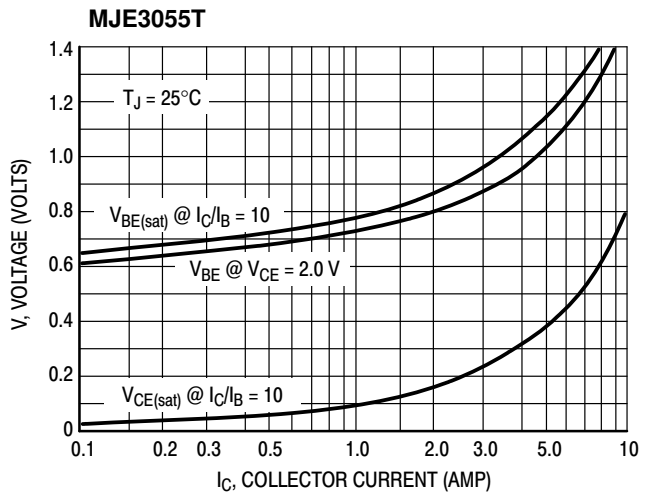
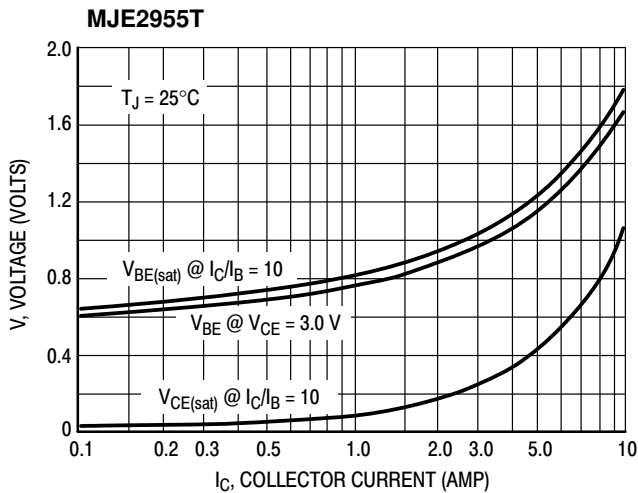
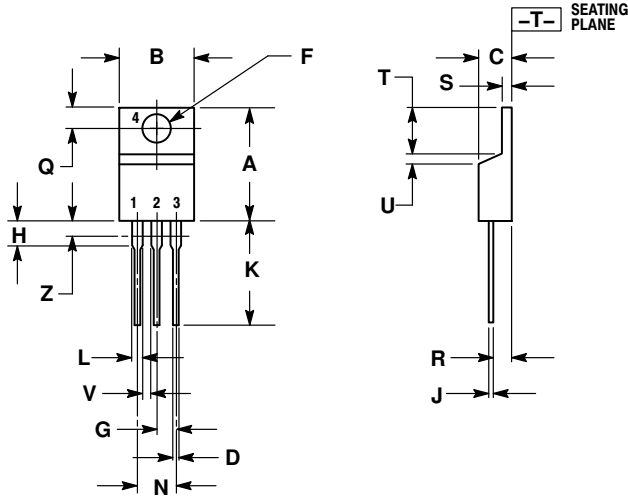


Figure 4. "On" Voltages

# MJE2955T (PNP), MJE3055T (NPN)

## PACKAGE DIMENSIONS

TO-220  
CASE 221A-09  
ISSUE AH




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### PUBLICATION ORDERING INFORMATION

**LITERATURE FULFILLMENT:**

Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
Email: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)

**Order Literature:** <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative